BTA316-600ET

3Q Hi-Com Triac

Rev. 02 — 29 November 2010

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package. The "series ET" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series ET" is intended for interfacing with low power drivers including microcontrollers where "high junction operating temperature" capability is required.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	140	Α
Tj	junction temperature		-	-	150	°C



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{T(RMS)}$	RMS on-state current	full sine wave; T _{mb} ≤ 126 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	16	Α
Static char	acteristics					
l _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{ Company of the company o$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 7}}{\text{C}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 7}}$	-	-	10	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N
2	T2	main terminal 2	mb	T2T1
3	G	gate		`G sym051
mb	T2	mounting base; main terminal 2	1 2 3	
			SOT78 (TO-220AB))

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA316-600ET	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{array}{c} V_{DRM} & \text{repetitive peak off-state voltage} \\ I_{T(RMS)} & RMS \text{ on-state current} \\ I_{T(RMS)} & RMS \text{ on-state current} \\ I_{TSM} & \text{non-repetitive peak on-state} \\ \text{current} & \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 20 ms;} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ \text{full sine wave; $T_{j(init)} = 25 \text{ °C; $t_p = 16.7 ms} \\ full sine wave; $T_{j($						
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Max	Unit
$I_{TSM} \text{non-repetitive peak on-state} \begin{cases} \text{full sine wave; } T_{j(\text{init})} = 25 \text{ °C; } t_p = 20 \text{ ms;} \\ \text{see } Figure 4; \text{see } Figure 5 \end{cases} \begin{cases} \text{full sine wave; } T_{j(\text{init})} = 25 \text{ °C; } t_p = 16.7 \text{ ms} \end{cases} \begin{cases} \text{loomedays} \text$	V_{DRM}	repetitive peak off-state voltage		-	600	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{T(RMS)}	RMS on-state current		-	16	Α
I^2t $I2t$ for fusing $t_p = 10$ ms; sine-wave pulse-98 A^2s dI_T/dt rate of rise of on-state current $I_T = 20$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/μs-100 $A/μs$ I_{GM} peak gate current-2A P_{GM} peak gate power-5W $P_{G(AV)}$ average gate powerover any 20 ms period-0.5W T_{stg} storage temperature-40150°C	I _{TSM}			-	140	Α
dI _T /dt rate of rise of on-state current I _T = 20 A; I _G = 0.2 A; dI _G /dt = 0.2 A/ μ s - 100 A/ μ s I _{GM} peak gate current - 2 A P _{GM} peak gate power - 5 W P _{G(AV)} average gate power over any 20 ms period - 0.5 W T _{stg} storage temperature -40 150 °C			full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	150	Α
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	I ² t	I2t for fusing	t _p = 10 ms; sine-wave pulse	-	98	A ² s
P _{GM} peak gate power - 5 W P _{G(AV)} average gate power over any 20 ms period - 0.5 W T _{stg} storage temperature -40 150 °C	dl _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
$P_{G(AV)}$ average gate power over any 20 ms period - 0.5 W T_{stg} storage temperature -40 150 °C	I _{GM}	peak gate current		-	2	Α
T _{stg} storage temperature -40 150 °C	P_{GM}	peak gate power		-	5	W
ssgg	$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _j junction temperature - 150 °C	T _{stg}	storage temperature		-40	150	°C
	Tj	junction temperature		-	150	°C

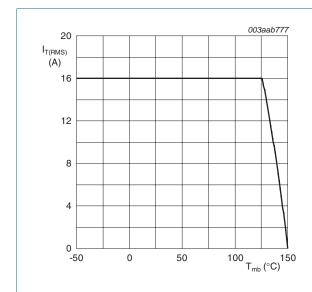
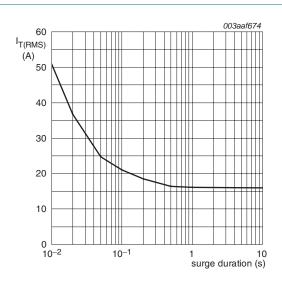


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{\text{mb}} = 126 \text{ }^{\circ}C$

Fig 2. RMS on-state current as a function of surge duration; maximum values

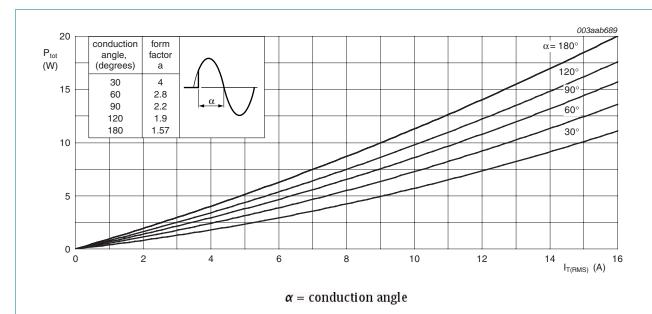


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

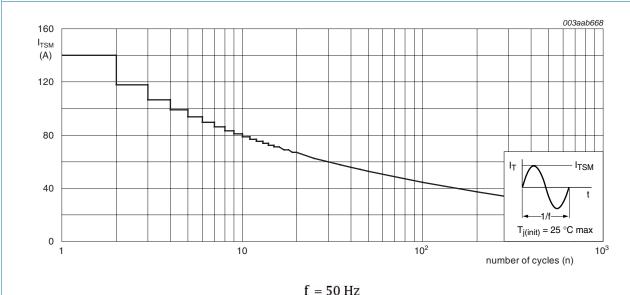
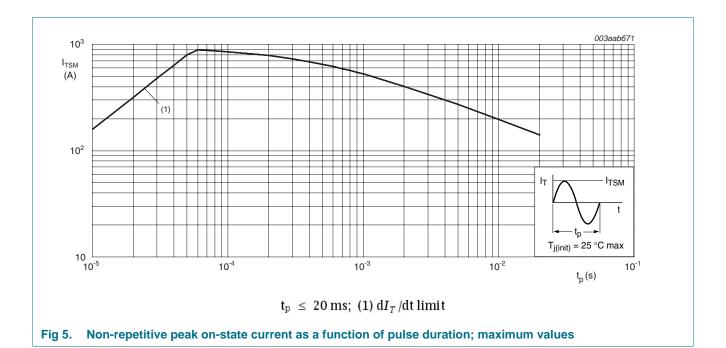


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	full cycle; see Figure 6	-	-	1.2	K/W
	mounting base	half cycle; see Figure 6	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

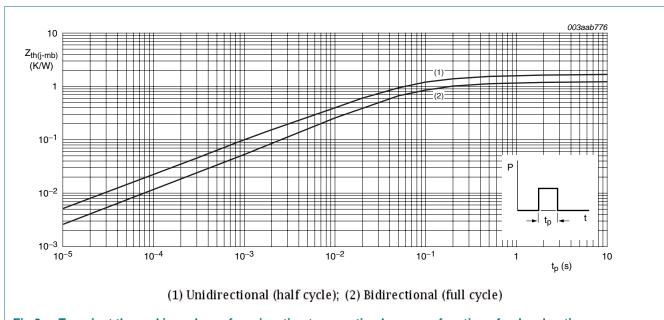


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see <u>Figure 7</u>	-	-	10	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; see <u>Figure 7</u>	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-; T_j = 25 °C;$ see Figure 7	-	-	10	mA
IL	L latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+G-; T_j = 25 °C;$ see <u>Figure 8</u>	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	30	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	15	mΑ
V_{T}	on-state voltage	$I_T = 18 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 °C;$ see Figure 11	0.25	-	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.24	1.2	mΑ
Dynamic o	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; exponential waveform; gate open circuit	20	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit}$	1.2	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/ μ s; "without snubber" condition; gate open circuit	0.8	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 1 V/µs; gate open circuit	6	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs

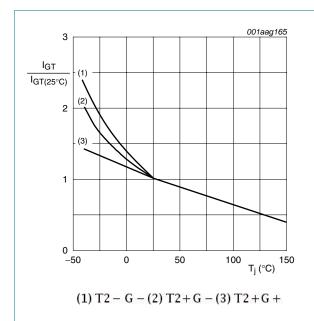


Fig 7. Normalized gate trigger current as a function of junction temperature

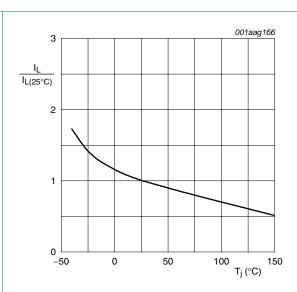


Fig 8. Normalized latching current as a function of junction temperature

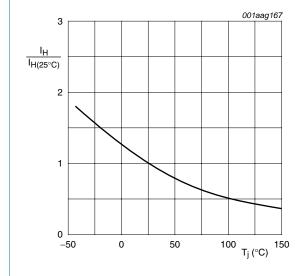
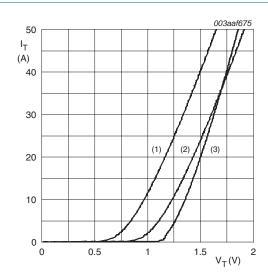


Fig 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.024 \text{ V}$

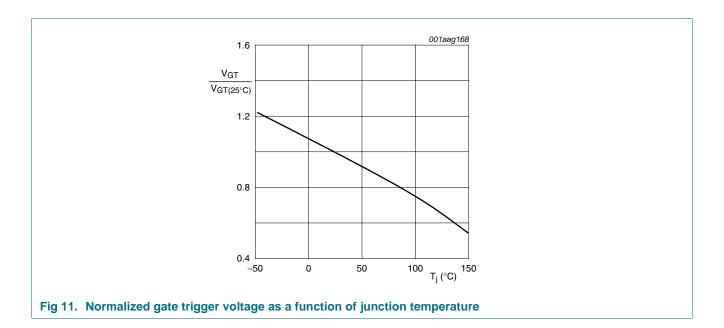
 $R_s = 0.021 \Omega$

(1) T_i = 150 °C; typical values

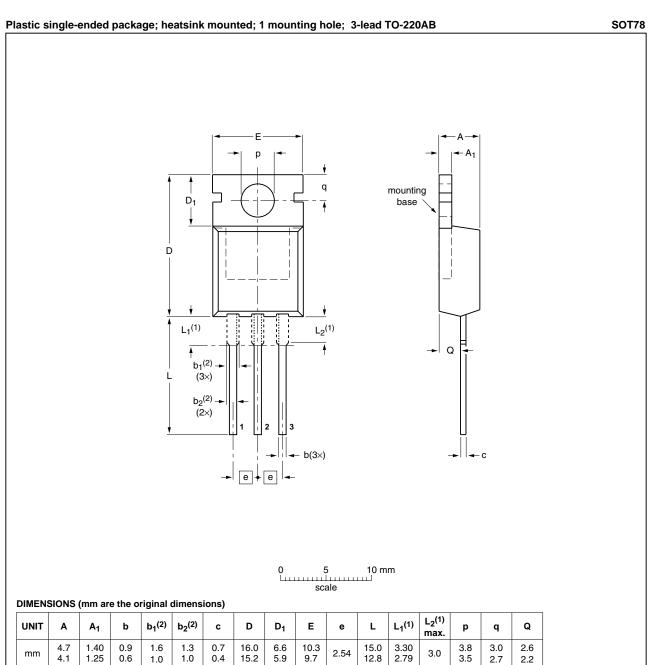
(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 12. Package outline SOT78 (TO-220AB)

BTA316-600ET

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316-600ET v.2	20101129	Product data sheet	-	BTA316-600ET v.1
Modifications:	 Various change 	es to content.		
BTA316-600ET v.1	20100330	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics6
6	Characteristics7
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13

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